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	APPLICANT Masahiko TANAKA et al.	
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	SECOND INFORMATION DISCLOSURE STATEMENT BY APPLICANT	

U.S. PATENT DOCUMENTS				
Examiner Initials	Document Number	Kind Code (if known)	Name of Patentee or Applicant of Cited Document	Issue/Publication Date (MM-DD-YYYY)
<i>KL</i>	5,433,787		Suzuki et al.	07-18-1995
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<i>o</i>	5,336,326		Karner et al.	08-09-1994
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Examiner Initials	Document Number	Kind Code (if known)	Country	Date of Publication (MM-DD-YYYY)	Translation Yes No
<i>KL</i>	8-167596		JAPAN	06-25-1996	<i>abs</i> X
<i>c</i>	2-601127		JAPAN	01-29-1997	X
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<i>c</i>	2837087		Japan	10-09-1998	X

NON PATENT LITERATURE DOCUMENTS	
Examiner Initials	Include name of author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.
<i>KL</i>	Robert C. REID et al. "Lennard-Jones Potentials as Determined from Viscosity Data (Appendix B)", <i>The Properties of Gases and Liquids</i> , McGraw-Hill, Inc., Copyright 1987, p.734, Index
<i>KL</i>	R. Byron BIRD et al. "Diffusivity and the Mechanisms of Mass Transport; Theory of Ordinary Diffusion in Gases at Low Density", <i>Transport Phenomena</i> , John Wiley & Sons, Inc., Copyright 1960, p. 508-513
<i>KL</i>	A new technique for diagnostics of a radio-frequency parallel-plate remote plasma; N. Sano et al.; Appl. Phys. Lett 65 (2), 11 July 1994 pages 162-164.
<i>KL</i>	Infrared spectroscopic study of SiO _x films produced by plasma enhanced chemical vapor deposition; J. Vac.Sci. Technol. A4(3), May/June 1986; pages 689-694.
<i>KL</i>	Improvement of structural and electrical properties in low-temperature gate oxides for poly-Si TFTs by controlling O ₂ /SiH ₄ ratios; AM-LCD 1997; pages 87-90.
<i>KL</i>	"Flow of Atoms and Molecules—Rarefied Gas Dynamics and its Applications", section 2.6.4, The Japan Society of Mechanical Engineers, 1996, Kyoritsu Shuppan Co., Ltd.
<i>KL</i>	Shingo KADOMURA et al., "ANISOTROPIC ETCHING USING DEPOSITION OF SULFUR, Sony Corporation, Semiconductor World, January 1993, pp. 1-11, and translation
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<i>KL</i>	Riccardo d'AGOSTINO et al., "PLASMA ETCHING OF Si and SiO ₂ in SF ₆ -O ₂ MIXTURES", J. Appl. Phys. 52(1), January 1981, pp. 162-167

Examiner Signature	<i>KAPLA MOORE</i>	Date Considered	<i>4/15/03</i>
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